

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Liming Tsau

Appl. No. 09/753,664

Filed: January 4, 2001

For: **High Density Metal Capacitor Using
Via Etch Stopping Layer as Field
Dielectric in Dual-Damascene
Interconnect Process**

Confirmation No.: 1902

Art Unit: 2823

Examiner: Brairton, Scott A.

Atty. Docket: 1875.0230000

Amendment And Reply Under 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In reply to the Office Action dated **March 27, 2002**, (PTO Prosecution File Wrapper Paper No. 6), Applicant submits the following Amendment and Remarks. This Amendment is provided in the following format:

- (A) A clean version of each replacement paragraph/section/claim along with clear instructions for entry;
- (B) Starting on a separate page, appropriate remarks and arguments. 37 C.F.R. § 1.121 and MPEP 714; and
- (C) Starting on a separate page, a marked-up version entitled: "Version with markings to show changes made."

It is not believed that extensions of time or fees for net addition of claims are required beyond those that may otherwise be provided for in documents accompanying this paper. However, if additional extensions of time are necessary to prevent abandonment of



1875.0230000

Amended
A
7/22/02
VLS